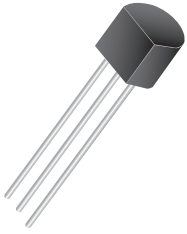
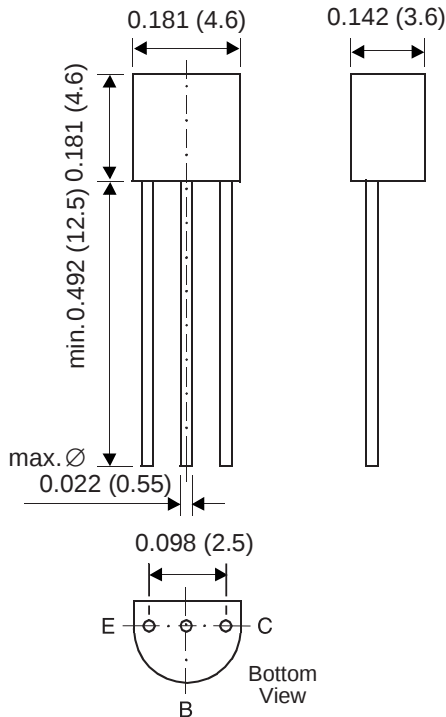




Small Signal Transistors (PNP)



TO-226AA (TO-92)



Dimensions in inches and (millimeters)

Features

- PNP Silicon Epitaxial Planar Transistors for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages such as portable radios in class-B push-pull operation.
- Complementary to GS9013

Mechanical Data

Case: TO-92 Plastic Package

Weight: approx. 0.18g

Packaging Codes/Options:

E6/Bulk-5K per container, 20K per box

E7/4K per Ammo mag., 20K per box

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	625 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	200 ⁽¹⁾	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Notes:

(1) Valid provided that leads are kept at ambient temperature at a distance of 2mm from case

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current Gain Group	D E F G H	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	64 78 96 112 144	— — — — —	91 112 135 166 202	—
DC Current Gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	40	90	—	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-20	—	—	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5	—	—	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -25\text{V}, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$	—	—	-100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	—	-0.18	-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$	—	-0.95	-1.2	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$	-0.6	-0.67	-0.7	V